

microelectronics reliability: physics-of-failure based ... - national aeronautics and space administration microelectronics reliability: physics-of-failure based modeling and lifetime evaluation nasa electronic parts and packaging (nepp) program

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mosfet small-signal model - prenhall - ee 105 spring 1997 lecture 12 mosfet small-signal model concept: find an equivalent circuit which interrelates the incremental changes in i_d

a comparison of electrostatic discharge models and failure ... - 4.2. 1 eos/esd symposium 95-175 a comparison of electrostatic discharge models and failure signatures for cmos integrated circuit devices m. kelly

an-1028 maximum power enhancement techniques for power ... - conclusion ti plots in figure 3 show the relationship of $r_{\theta jc}$ versus the copper mounting pad area and its surface placement on the board. it is apparent that increasing copper mounting pad area considerably lowers $r_{\theta jc}$ from approximately $110^\circ\text{C}/\text{w}$ to $40^\circ\text{C}/\text{w}$ in the range from 0.0123 to 1 square inches.

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design of a voltage-controlled ring oscillator based on ... - fig.6 output swing with different value of v_{con} . phase noise because the tuning mos capacitor almost has no effect on whole circuit, when changing the working frequency, the

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comparison of pam-4 and nrz signaling - ieee 802 - authors david r stauffer, ph.d. is the chair of the uxpi [1] technical council, and is a senior engineer with ibm microelectronics. stephen d. anderson is the uxpi editor, and is a staff engineer

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